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Extreme charge transfer in the misfit layered compound (LaSe)_{1.14}(NbSe₂)

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Misfit materials

Naturally layered crytals Unit cell is stabilized by electron transport from MX part to TX₂

MX = LaSe

 $TX_2 = NbSe_2$

Superconductors! (LaSe)_{1.14}(NbSe₂) 1Q1H; T_c ~ 1.2 K

 $(LaSe)_{1.14}(NbSe_2)_{2}$ 1Q2H; $T_c \sim 5 K$





Upper critical magnetic field





Bulk superconductivity is confirmed by heat capacity measurements





Iono-covalent bonds





- Bulk VdW system consisting of weakly interacting 2D layers. These 2D layers are equivalent of extremely doped NbSe₂ monolayer.
- Such extreme doping is not achievable by other means (FET, K/Na deposition ...)
- Tunable by Pb \rightarrow La substitution.
- ML NbSe₂ is non-centrosymetric system \rightarrow electron spins are locked in out-of plane direction (**Ising superconductivity**) \rightarrow H_{c2||ab} >> H_P

ADVANCEDFUNCTIONAL **MATERIALS**

Full Paper 🛛 🔂 Full Access

Misfit Layer Compounds: A Platform for Heavily Doped 2D Transition Metal Dichalcogenides

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Structure and bonding 1Q1H



- Breaking @Q into Q*
- Q* surface: unstable, ordered only at N2!



Fourier transform of atomically resolved surface is similar to diffraction methods (LEED)

QuasiParticle Interference

• Electrons can be described as Bloch wavefunctions + scattering \rightarrow interference \rightarrow standing wave pattern





Surface states, QPI 1Q2H – 1Q1H







H + Q* surface band structure ARPES

 Preliminary estimate: shift ~200meV compared to 1Q2H (H surface) due to Q* "impurities" surface doping ???



Wen-Yu He, et al., Communications Physics 1, 40 (2018)

1Q2H = H 1Q1H = H + Q*



DFT bulk **1Q1H**

- 2x doping compared to 1Q2H
- NbSe₂ insulating
- LaSe conducting
- Bulk SC from heat capacity
- SC in LaSe



Surface STM & STS



Small surface superconducting gap



Bulk STM & STS

 gap consistent with transport and heat capacity

Upper critical magnetic field









Conclusions



1Q2H

- VdW crystal
- Decoupled doped NbSe₂ monolayers
 - Bulk Ising SC from noncentrosymmetric NbSe₂ → H_{c2||ab} >> H_p

1Q1H

- Ionocovalent bonds between layers
- Even higher doping → superconducting LaSe is decoupled by insulating NbSe₂ monolayers
- LaSe is centrosymmetric \rightarrow why is $H_{c2||ab} >> H_{p}$?



Acknowledgments



Thank you for your attention!